

# **isc Silicon NPN Power Transistor**

## 2SD2406

#### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 80V(Min)
- · Collector Power Dissipation-
  - : P<sub>C</sub>= 25W@ T<sub>C</sub>= 25℃
- Good Linearity of h<sub>FE</sub>
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

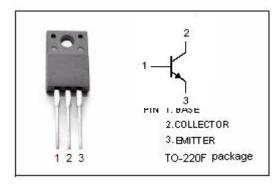


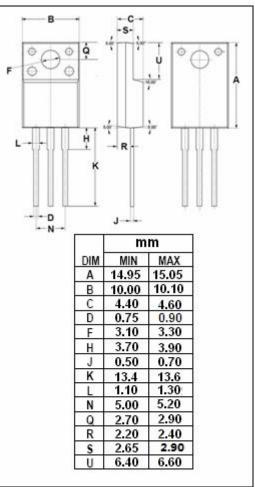
#### **APPLICATIONS**

· Designed for power amplifier applications.



SYMBOL	PARAMETER	VALUE	UNIT
V <sub>СВО</sub>	Collector-Base Voltage	80	V
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current-Continuous	4	Α
I <sub>B</sub>	Base Current-Continuous	0.4	Α
Pc	Collector Power Dissipation @T <sub>C</sub> =25℃	25	W
TJ	Junction Temperature	mperature 150	
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$







#### isc Silicon NPN Power Transistor

2SD2406

#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	80			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.3A			1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 80V; I <sub>E</sub> = 0			30	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V	70		240	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	15			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1MHz		90		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V		8		MHz

### ♦ h<sub>FE-1</sub> Classifications

0	Y		
70-140	120-240		

#### **NOTICE:**

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

isc website: www.iscsemi.cn

isc & iscsemi is registered trademark